

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1-15. (Canceled).

16. (Currently amended) A substrate treatment method comprising:
coating a substrate with a photosensitive resist film;
exposing said photosensitive resist film;
supplying a reducing solution to the surface of said exposed photosensitive resist film and performing a pretreatment;
developing the photosensitive resist film subjected to said pretreatment; and
supplying a cleaning solution to said substrate, and cleaning the substrate;
wherein the reducing solution is an aqueous solution containing at least one of hydrogen, H_2S , HNO_3 , and H_2SO_3 .

17. (Canceled)

18. (Original) The substrate treatment method according to claim 16, further comprising: discharging the developing solution to said photosensitive resist film from a developing solution supply nozzle; relatively moving said substrate and said developing solution supply nozzle; forming a developing solution film on the surface of the photosensitive resist film; and developing said photosensitive resist film.

19. (Original) The substrate treatment method according to claim 18, further comprising: agitating said developing solution film; and developing said photosensitive resist film.

20. (Original) The substrate treatment method according to claim 16, further comprising: removing said reducing solution from the surface of said photosensitive resist film after said pretreatment; drying the surface of the resist film; and developing said photosensitive resist film.

21. (Original) The substrate treatment method according to claim 18, further comprising: forming said developing solution film on the resist film surface in a state in which said reducing solution remains on the surface of said photosensitive resist film after said pretreatment; agitating the remaining solution and the developing solution; and developing said photosensitive resist film.

22-37. (Canceled).

38. (Currently amended) A manufacturing method of a semiconductor device, comprising:

coating a substrate with a photosensitive resist film;

exposing said photosensitive resist film;

supplying a reducing solution to the surface of said exposed photosensitive resist film and performing a pretreatment;

developing the photosensitive resist film subjected to said pretreatment; and
supplying a cleaning solution onto said substrate, and cleaning the substrate;
wherein the reducing solution is an aqueous solution containing at least one of
hydrogen, H_2S , HNO_3 , and H_2SO_3 .

39-43. (Canceled).